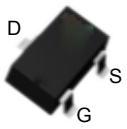
Features

- 30V/3.6A
  $R_{DS(ON)}$=20mΩ(typ.)@V_{GS}=10V
  $R_{DS(ON)}$=26mΩ(typ.)@V_{GS}=4.5V
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

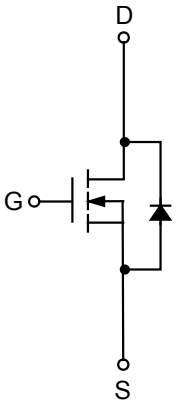
Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems
- Load Switch

Pin Description



SOT-23



N-Channel MOSFET

Absolute Maximum Ratings (T_A=25°C Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		±20	
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	
I_S	Diode Continuous Forward Current	T_A=25°C	3.6	A
I_D	Continuous Drain Current	T_A=25°C	3.6	A
		T_A=70°C	2.7	
I_{DM} [a]	Pulsed Drain Current	T_A=25°C	10.8	
P_D [b]	Maximum Power Dissipation	T_A=25°C	1.2	W
		T_A=70°C	0.8	
$R_{\theta JA}$ [b]	Thermal Resistance-Junction to Ambient	t ≤ 10s	67	°C/W
		Steady state	102	
I_{AS} [c]	Avalanche Current, Single pulse	L=0.1mH	7.3	A
E_{AS} [c]	Avalanche Energy, Single pulse	L=0.1mH	2.7	mJ

Note a：Pulse width limited by max. junction temperature.
Note b：Surface mounted on 1in^2 pad area, steady state t = 999s.
Note c：UIS tested and pulse width limited by maximum junction temperature (initial temperature T_j=25°C).

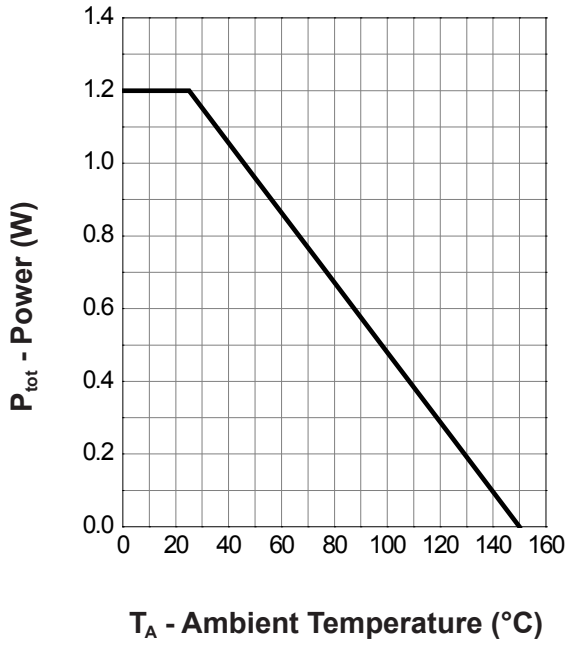
Electrical Characteristics (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250μA	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=24V, V_{GS}=0V	-	-	1	μA
		T_J=85°C	-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250μA	1.0	1.5	2.0	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
$R_{DS(ON)}$ [d]	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=4A	-	20	25	mΩ
		T_J=125°C	-	53	-	
		V_{GS}=4.5V, I_{DS}=3A	-	26	31	
		V_{GS}=2.5V, I_{DS}=2A	-	35	45	
Gfs	Forward Transconductance	V_{DS}=5V, I_{DS}=3A	-	5.6	-	S
Diode Characteristics [e]						
V_{SD} [d]	Diode Forward Voltage	I_{SD}=1A, V_{GS}=0V	-	0.75	-	V
t_{rr}	Reverse Recovery Time	I_{SD}=4A, dI_{SD}/dt=100A/μs	-	8.7	-	ns
t_a	Charge Time		-	3.4	-	
t_b	Discharge Time		-	4	-	
Q_{rr}	Reverse Recovery Charge		-	5	-	nC
Dynamic Characteristics [e]						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V,F=1MHz	-	5.5	-	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, Frequency=1.0MHz	-	280	-	pF
C_{oss}	Output Capacitance		-	39	-	
C_{rss}	Reverse Transfer Capacitance		-	30	-	
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=15V, R_L=15Ω, I_{DS}=1A, V_{GEN}=10V, R_G=6Ω	-	5.6	10.1	ns
t_r	Turn-on Rise Time		-	11	19.8	
$t_{d(OFF)}$	Turn-off Delay Time		-	18	32.4	
t_f	Turn-off Fall Time		-	3.2	5.8	
Gate Charge Characteristics [e]						
Q_g	Total Gate Charge	V_{DS}=15V, V_{GS}=10V, I_{DS}=4A	-	7	-	nC
Q_{gth}	Threshold Gate Charge		-	0.4	-	
Q_{gs}	Gate-Source Charge		-	0.7	-	
Q_{gd}	Gate-Drain Charge		-	1	-	

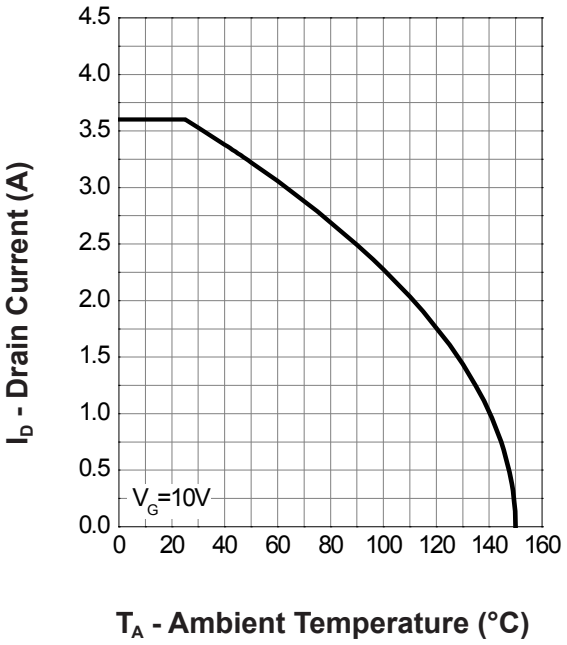
Note d：Pulse test ; pulse width≤300μs, duty cycle≤2%.
Note e：Guaranteed by design, not subject to production testing.nd on package type.

Typical Operating Characteristics

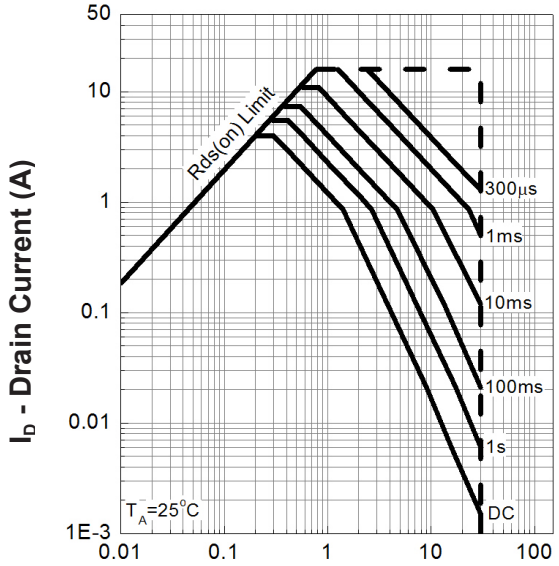
Power Dissipation



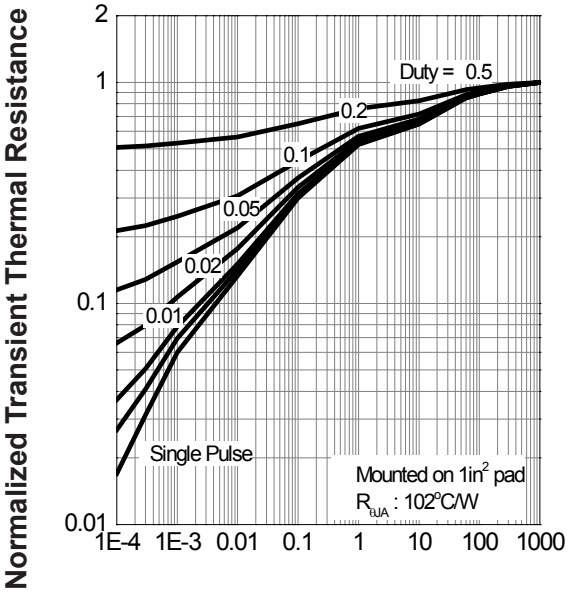
Drain Current



Safe Operation Area

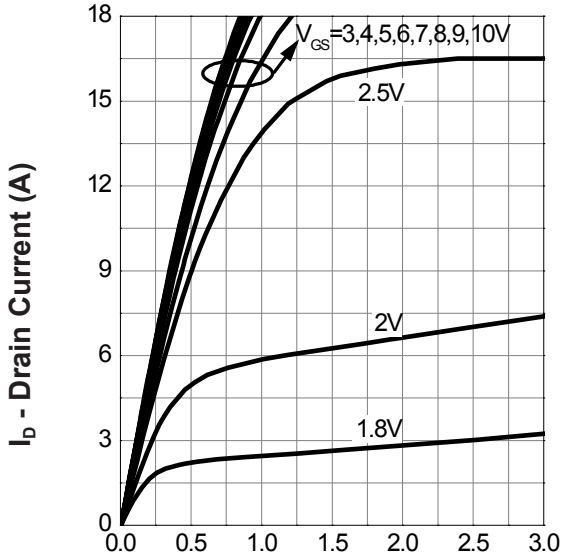


Thermal Transient Impedance

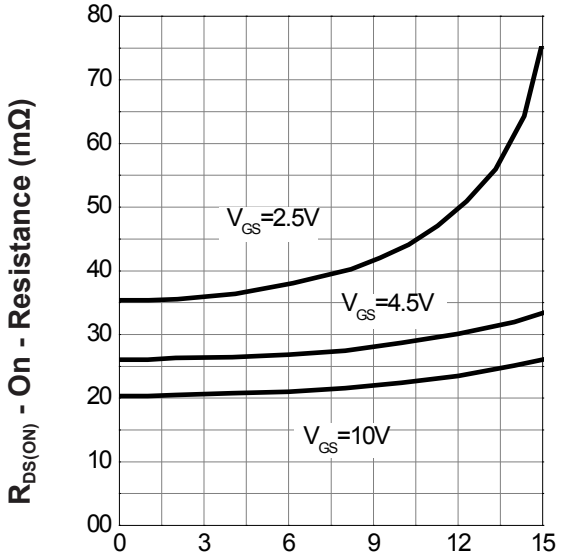


Typical Operating Characteristics(Cont.)

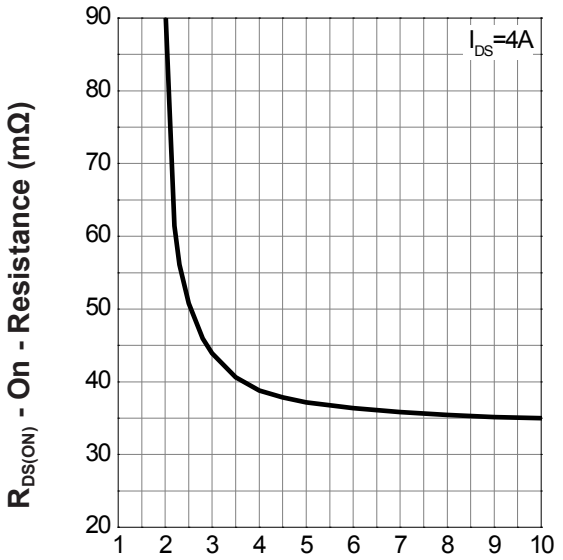
Output Characteristics



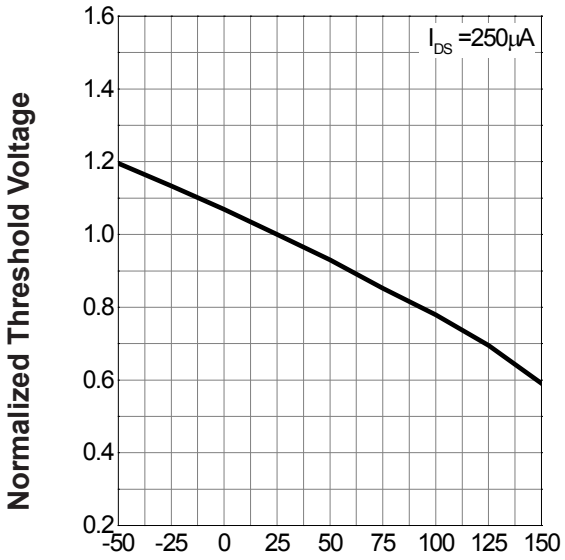
Drain-Source On Resistance



Gate-Source On Resistance

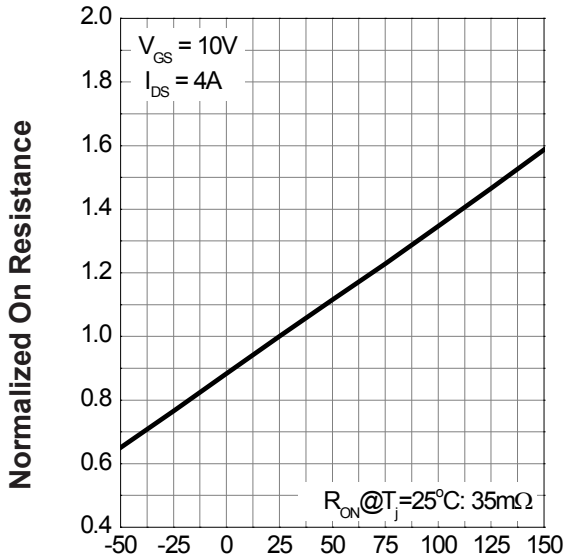


Gate Threshold Voltage

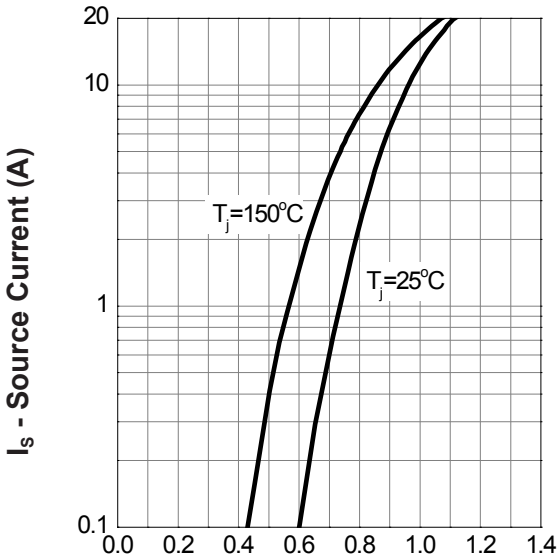


Typical Operating Characteristics(Cont.)

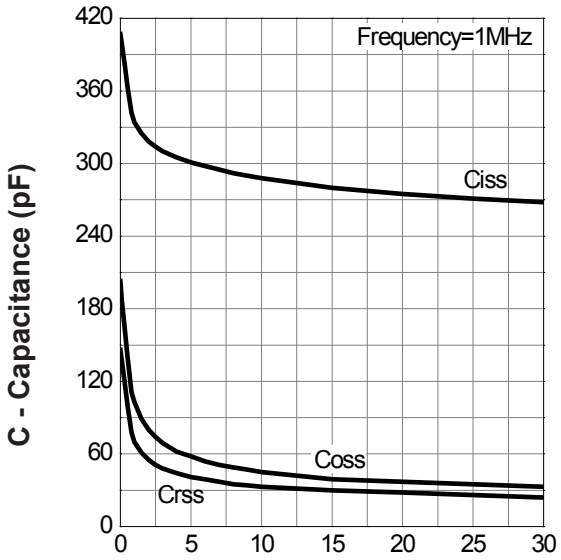
Drain-Source On Resistance



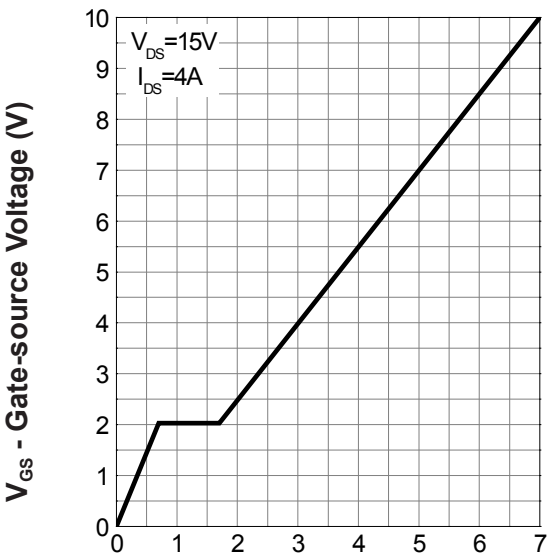
Source-Drain Diode Forward



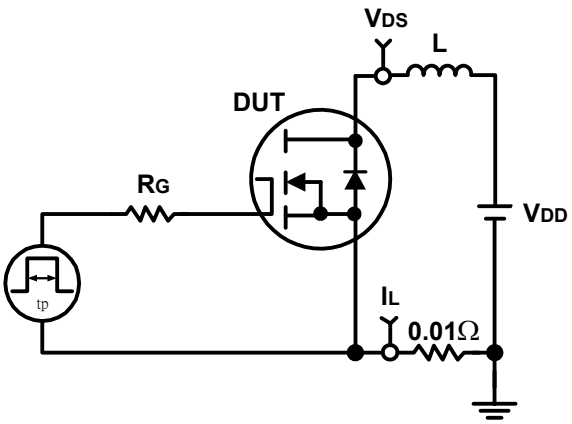
Capacitance

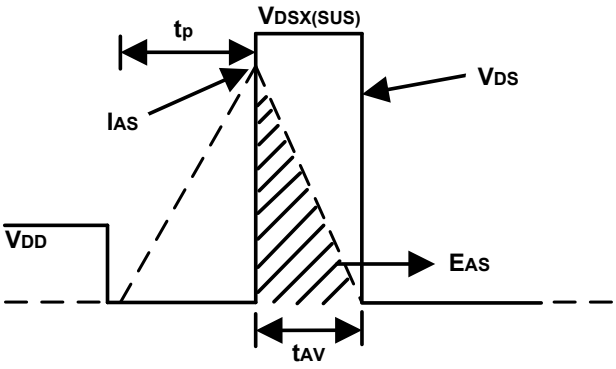


Gate Charge

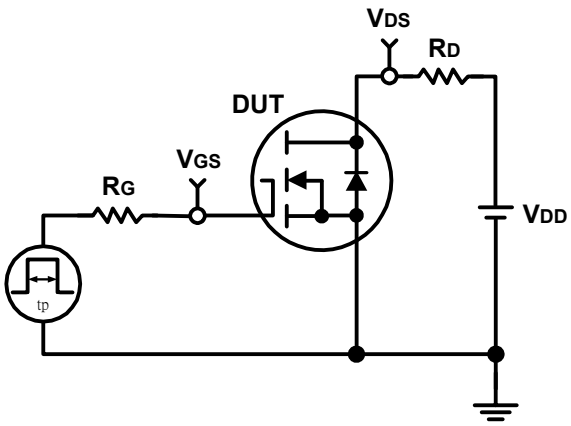


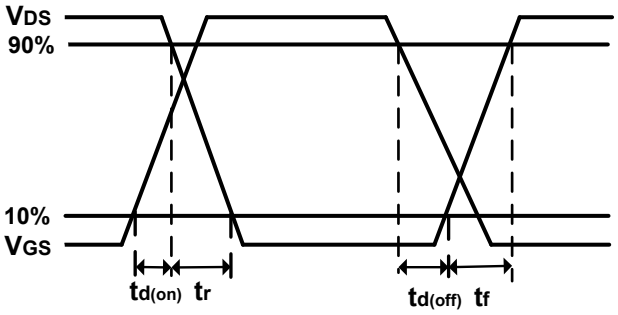
Avalanche Test Circuit and Waveforms





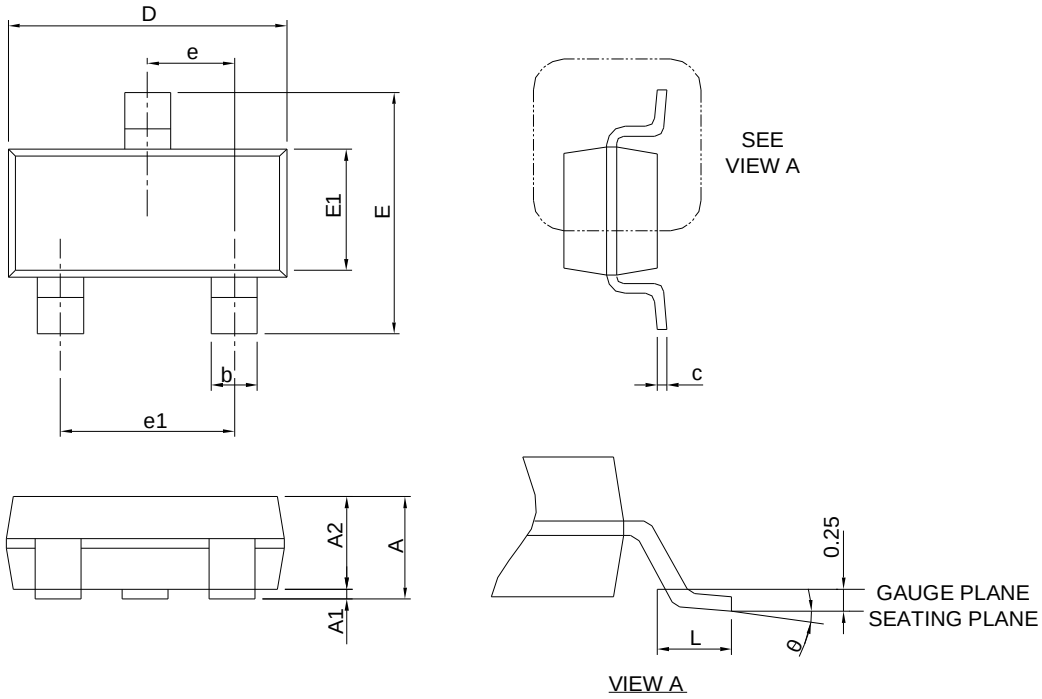
Switching Time Test Circuit and Waveforms





Package Information

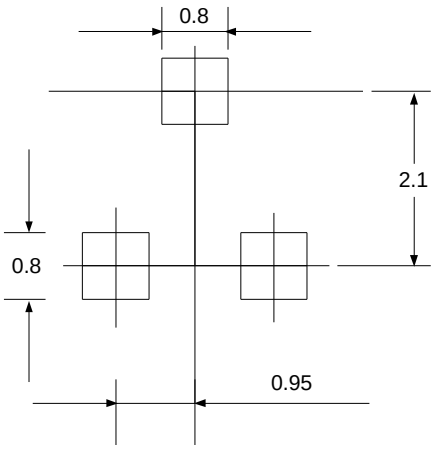
SOT-23



SYMBOL	SOT-23			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	-	1.20	-	0.047
A1	0.00	0.10	0.000	0.004
A2	0.90	1.10	0.035	0.043
b	0.30	0.50	0.012	0.020
c	0.08	0.22	0.003	0.009
D	2.70	3.10	0.106	0.122
E	2.20	2.60	0.086	0.102
E1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.037 BSC	
e1	1.90 BSC		0.075 BSC	
L	0.30	0.60	0.012	0.024
θ	0 °	8 °	0 °	8 °

Note : Dimension D and E1 do not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 10 mil per side.

RECOMMENDED LAND PATTERN



UNIT: mm